

**SANYO**

No. 1614B

**2SC3636**

NPN Triple Diffused Planar Silicon Transistor  
 VERY HIGH-DEFINITION DISPLAY  
 HORIZONTAL DEFLECTION OUTPUT APPLICATIONS

**Features**

- . High reliability (Adoption of HVP process)
- . Fast speed.
- . High breakdown voltage.
- . Adoption of MBIT process.

**Absolute Maximum Ratings at Ta=25°C**

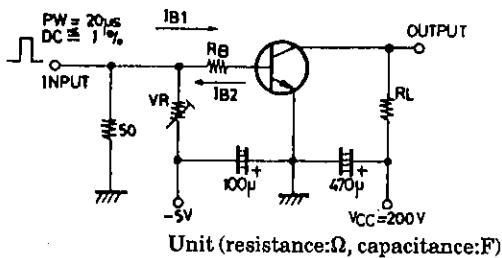
			unit
Collector-to-Base Voltage	V <sub>CB0</sub>	900	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>	500	V
Emitter-to-Base Voltage	V <sub>EB0</sub>	7	V
Collector Current	I <sub>C</sub>	7	A
Peak Collector Current	i <sub>cp</sub>	14	A
Collector Dissipation	P <sub>C</sub>	80	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Tc=25°C

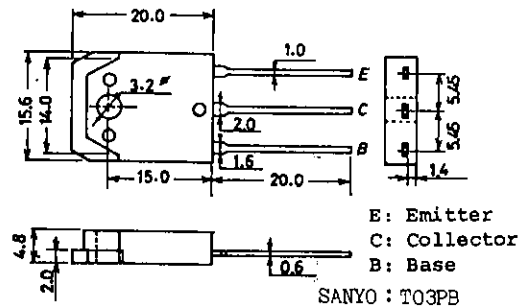
**Electrical Characteristics at Ta=25°C**

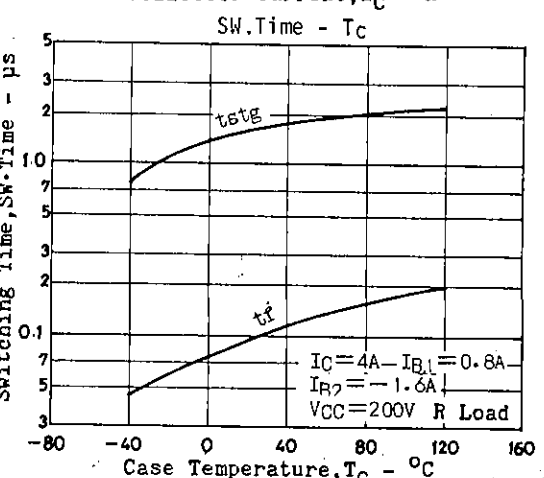
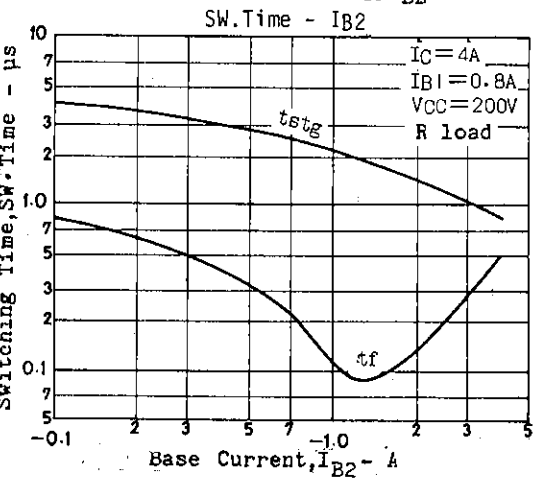
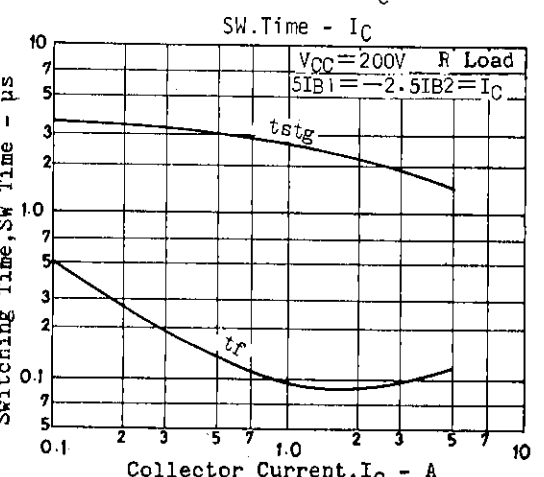
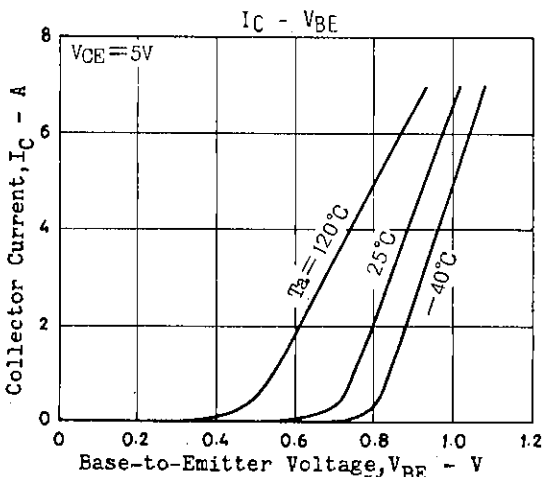
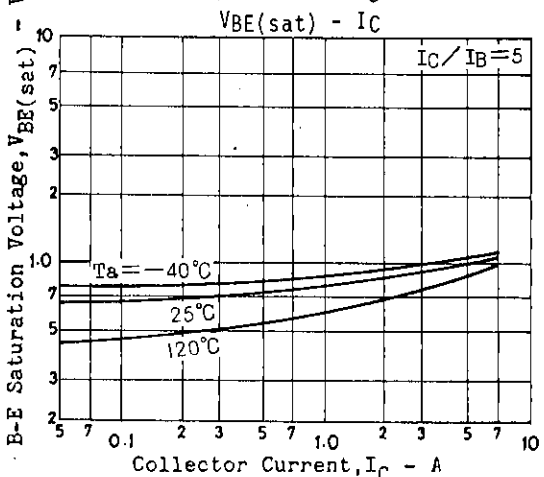
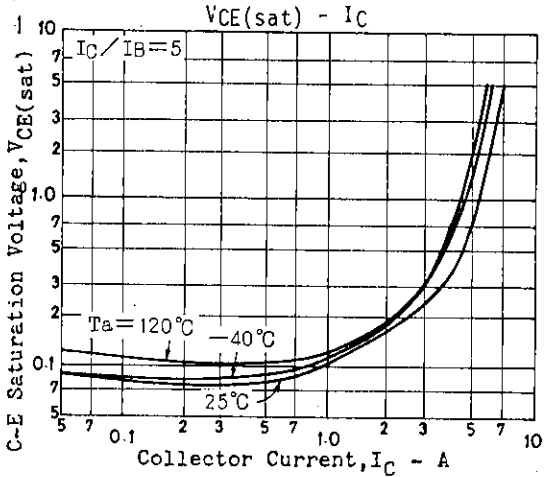
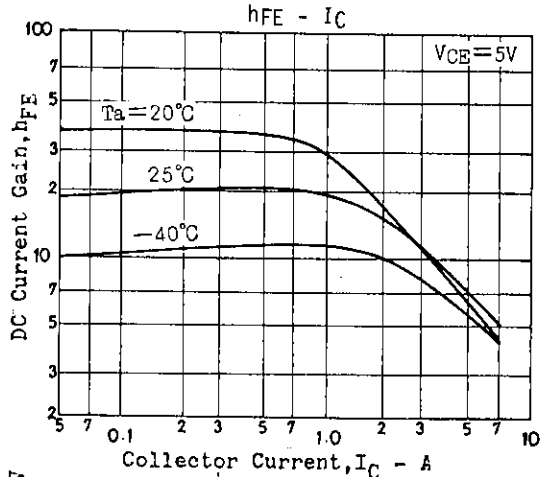
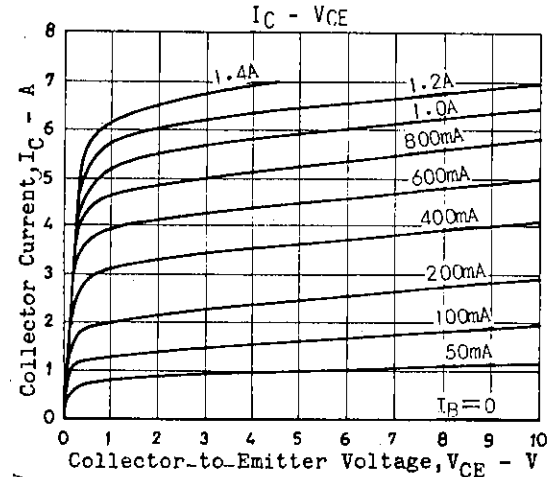
			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =500V, I <sub>E</sub> =0			10	µA
	I <sub>CES</sub>	V <sub>CE</sub> =900V, R <sub>BE</sub> =0			0.5	mA
Collector-to-Emitter Sustain Voltage	V <sub>CEO(sus)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =0	500			V
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			1	mA
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =4V, I <sub>B</sub> =0.8A			2	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.8A			1.5	V
DC Current Gain	f <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =0.8A	8			
Storage Time	t <sub>stg</sub>	I <sub>C</sub> =4A, I <sub>B1</sub> =0.8A, I <sub>B2</sub> =-1.6A			3.0	µs
Fall Time	t <sub>f</sub>	I <sub>C</sub> =4A, I <sub>B1</sub> =0.8A, I <sub>B2</sub> =-1.6A	0.1	0.2		µs

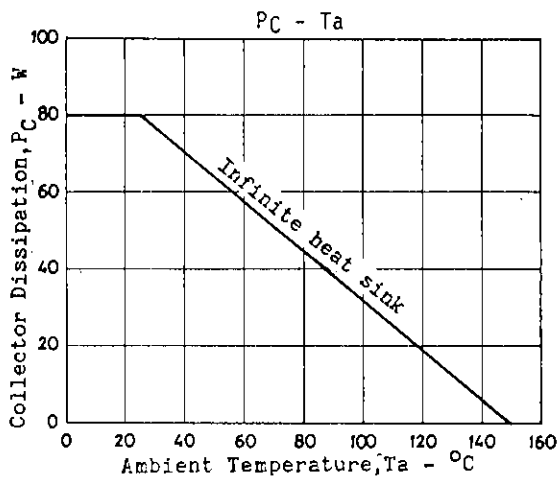
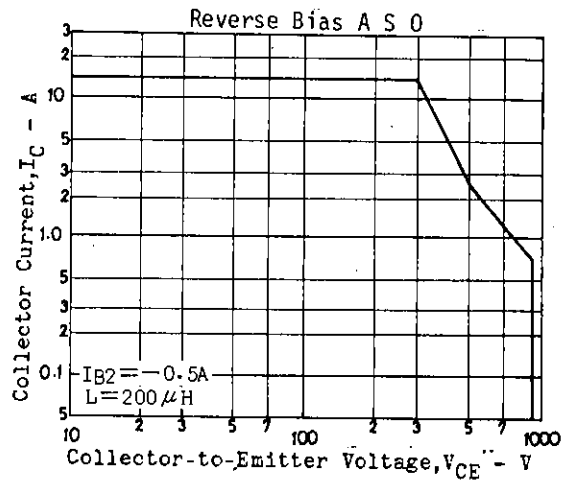
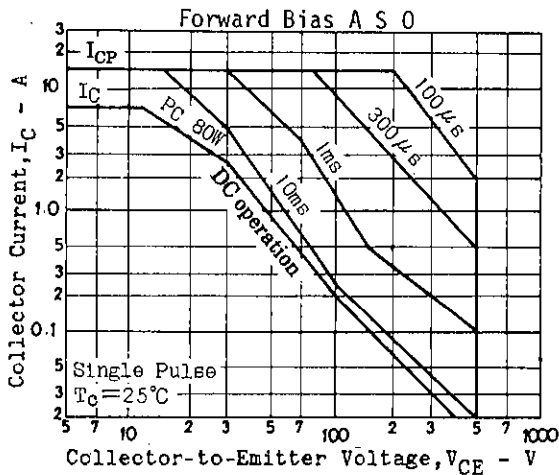
**Switching Time Test Circuit**



**Package Dimensions 2022 (unit: mm)**







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